

### **KSA1244**

# High Current Switching • Low Collector-Emitter Saturation Voltage • Complement to KSC3074



## **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	- 60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 50	V
$V_{EBO}$	Emitter-Base Voltage	- 5	V
I <sub>B</sub>	Base Current	- 1	Α
I <sub>C</sub>	Collector Current	- 5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -10 \text{mA}, I_B = 0$	- 50			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -50V, I_{E} = 0$			-1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			-1	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 1A V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 3A	70 30		240	
V <sub>CE</sub> (Sat)	Collector-Emitter Saturation Voltage	$I_C = -3A$ , $I_B = -0.15A$			-0.5	V
V <sub>BE</sub> (Sat)	Base-Emitter Saturation Voltage	$I_C = -3A$ , $I_C = -0.15A$		- 0.9	-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 4V, I <sub>C</sub> = - 1A		60		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = - 10V, f = 1MHz		170		pF
t <sub>ON</sub>	Turn ON Time	$V_{CC} = -30V, I_{C} = -3A$		0.1		μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = -0.15A$		1		μs
t <sub>F</sub>	Fall Time	$R_L = 10\Omega$		0.1		μs

### **h**<sub>FE</sub> Classification

Classification	0	Y	
h <sub>FE1</sub>	70 ~ 140	120 ~ 240	

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# **Typical Characteristics**

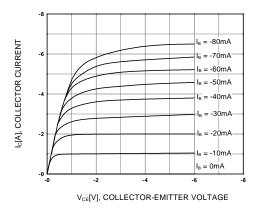


Figure 1. Static Characteristic

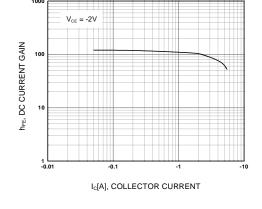


Figure 2. DC current Gain

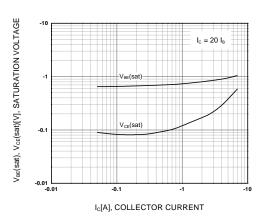


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

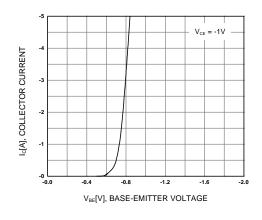


Figure 4. Base-Emitter Saturation Voltage

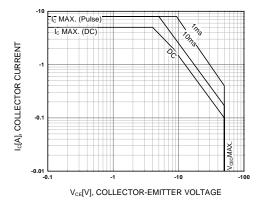


Figure 5. Safe Operating Area

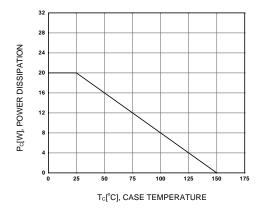
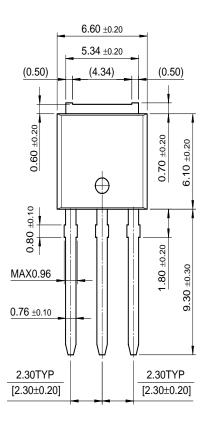


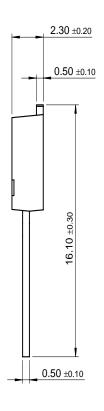
Figure 6. Power Derating

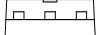
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# **Package Demensions**

# I-PAK







Dimensions in Millimeters

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